![D3 SEMICONDUCTOR® DEFINING PRECISION POWER]

+FET™

D3S280N65

650V, 280mΩ, 14.1 A Super Junction Power MOSFET

Ordering Information

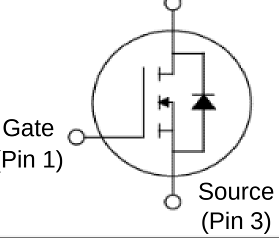
Part Number	Package Option
D3S280N65B-U	TO-220
D3S280N65E-T	TO-263
D3S280N65F-U	TO-220 FullPak (FP)

TO-220 TO-263 TO-220 FullPak

Description

+FET[TM] is an advanced Super Junction Power MOSFET offering excellent efficiency through low Rds-ON and low gate charge. +FET[TM] is a rugged device with precision charge balance implementation designed for demanding uses such as enterprise power computing power supplies, motor control, lighting and other challenging power conversion applications.

Device Schematic



LEAD-FREE RoHS

Features

- LOW $R_{DS(ON)}$
- FAST SWITCHING
- HIGH E_{AS}
- REL TEST SPEC: JESD-22
- LOW OUTPUT CAPACITANCE

Benefits

- LOW CONDUCTION LOSSES
- HIGH EFFICIENCY
- EXCELLENT AVALANCHE PERFORMANCE

Table 1 Key Performance Parameters

Parameters	Value	Unit
V_{DS} @ $T_{J\ max}$	710	V
RDS(on),max	<280	mΩ
Q_g ,typ	22	nC
$I_{D\ @\ 25C}$	14	A
Coss	41	pf

Applications

- POWER FACTOR CORRECTION
- SERVER POWER SUPPLIES
- TELECOM POWER SUPPLIES
- INVERTERS
- MOTOR CONTROL

Table of contents

@ T_J = 25ºC ,unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values				Unit	Note/Test Condition
		Min.	Typ.	Max.			
				220, 263 &247	220FP		
Continuous drain current(1)	I_D			14.1	7.8	A	T_C = 25ºC
				8.9	4.9		T_C = 100ºC
Pulsed drain current(2)	$I_{D,pulse}$			56.3	31.0	A	T_C = 25ºC
Avalanche energy, single pulse	E_{AS}			260	260	mJ	I_D=2.4A, V_{DD}=50V
Avalanche energy, repetitive	E_{AR}			0.65	0.65	mJ	I_D=2.4A, V_{DD}=50V
Avalanche current, repetitive	I_{AR}			2.4	2.4	A	
MOSFET dv/dt ruggedness	dv/dt			50	50	V/ns	V_{DS}=…480V
Gate source voltage	V_{GS}	-30		30	30	V	static
		-30		30	30		AC (f > 1HZ)
Power dissipation for TO-220	P_{tot}			147	45	W	T_C = 25ºC
Operating and storage temperature	T_j, T_{stg}	-55		150	150	ºC	
Mounting torque				60		Ncm	M3 and M3.5 screws
					50		M3 screws
Continuous diode forward current	I_S			14.1	7.8	A	T_C = 25ºC
Diode pulsed current	$I_{S,pulse}$			56.3	31.0	A	T_C = 25ºC
Reverse diode dv/dt(3)	dv/dt			15	15	V/ns	V_{DS}=…480V, I_{SD}<I_D T_J= 25ºC
Maximum diode commutation speed	dif/dt			500	500	A/us	

Table 3 Thermal characteristics

Parameter	Symbol	Values				Unit	Note/Test Condition
		Min.	Typ.	Max.			
				220, 263 &247	220FP		
Thermal resistance, Junction-case	R_{thJC}			1.0	3.1	ºC/W	
Thermal resistance, Junction-ambient	R_{thJA}			52	55	ºC/W	Leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}			260	260	ºC	1.6mm form case for 10s

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Drain to source breakdown voltage	$V_{(BR)DSS}$	650			V	V_{GS}=0V, I_D=1mA
Gate threshold voltage	$V_{GS(TH)}$	2.3	3.2	4.5	V	V_{DS}=V_{GS}, I_D=71.7uA
Zero gate voltage drain current	I_{DSS}			1	uA	V_{DS}=650V, V_{GS}=0V, T_J = 25°C
				40		V_{DS}=650V, V_{GS}=0V, T_J = 150°C
Gate to source leakage current	I_{GSS}			100	nA	V_{GS}=±20V, V_{DS}=0V
Drain-source on-state resistance	$R_{DS(On)}$		267	280	mΩ	V_{GS}=10V, I_D=7.1A, T_J = 25°C
			630		mΩ	V_{GS}=10V, I_D=7.1A, T_J = 150°C
Gate resistance	R_G		1.0		Ω	Scaf-F

Table 5 Dynamic characterristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}		800		pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Output capacitance	C_{oss}		39.7		pF	
Reverse transfer capacitance	C_{rss}		7.5		pF	
Effective output capacitance, energy related 1	$C_{o(er)}$		69		pF	V_{DS}=0…480V, V_{GS}= 0V
Effective output capacitance, time related 2	$C_{o(tr)}$		147		pF	I_D=constant, V_{DS}=0…480V, V_{GS}= 0V
Turn on delay time	$t_{d(on)}$		7		ns	V_{DD}=400V, I_D=7.1A, R_G=3.4Ω, V_{GS}=13V
Rising time	t_r		21		ns	
Turn off delay time	$t_{d(off)}$		21		ns	
Fall time	t_f		23		ns	

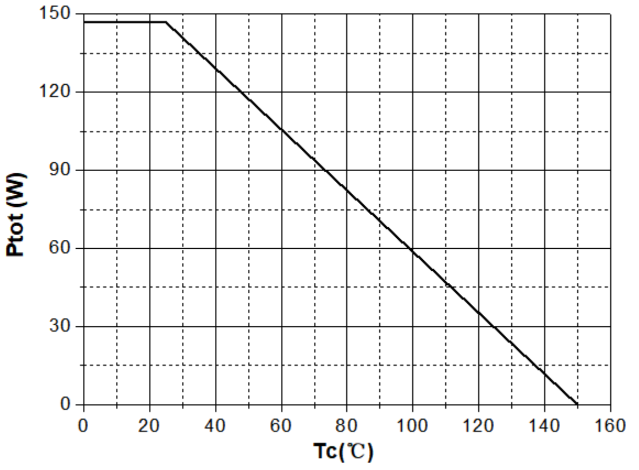
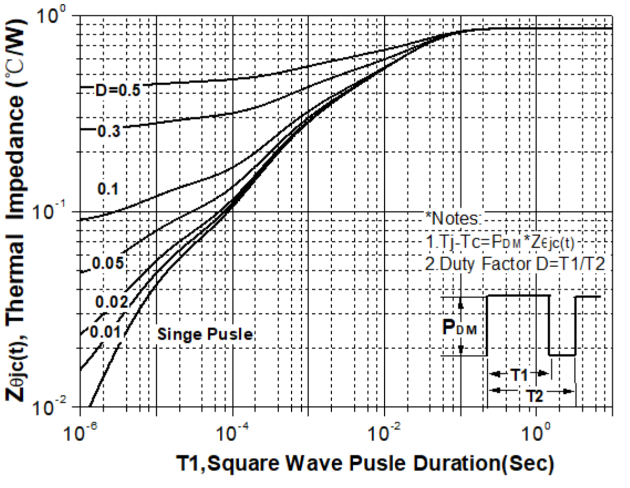
Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Total gate charge	Q_g		22		nC	V_{DD}=480V, V_{GS}=0 to10V I_D=7.1A
Gate-source charge	Q_{gs}		6.2		nC	
Gate-drain charge	Q_{gd}		9.5		nC	
Gate plateau voltage	$V_{plateau}$		5.0		V	

Table 7   Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}		0.85	0.96	V	I_F=14.1A, V_{GS}=0V, T_J = 25ºC
Reverse recovery time	t_{rr}		266		ns	I_F=14.1A,dI_F/dt=100A/us
Reverse recovery charge	Q_{rr}		2.8		uC	
Peak reverse recovery current	I_{rrm}		20		A	

Table 8 Thermal Performance

<table>
<tr><th>Power dissipation（TO220, TO263 & TO247）</th><th>Max. transient thermal impedance （TO220,TO263 & TO247）</th></tr>
<tr><td>
</td><td>
</td></tr>
<tr><td>$P_{tot}=f(T_C)$</td><td>$Z_{thJC}=f(t_P)$;parameter:$D=t_P/T$</td></tr>
</table>

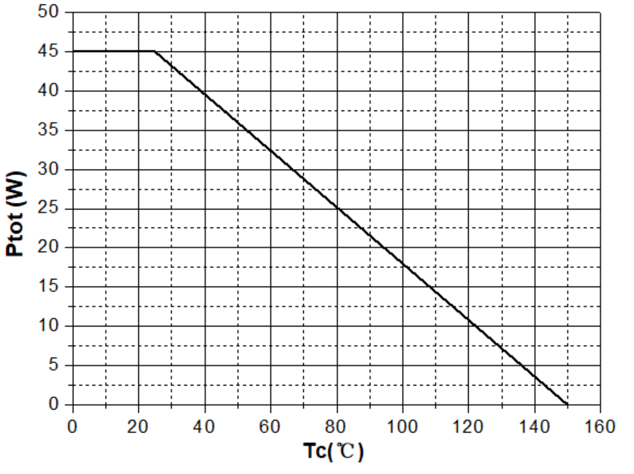
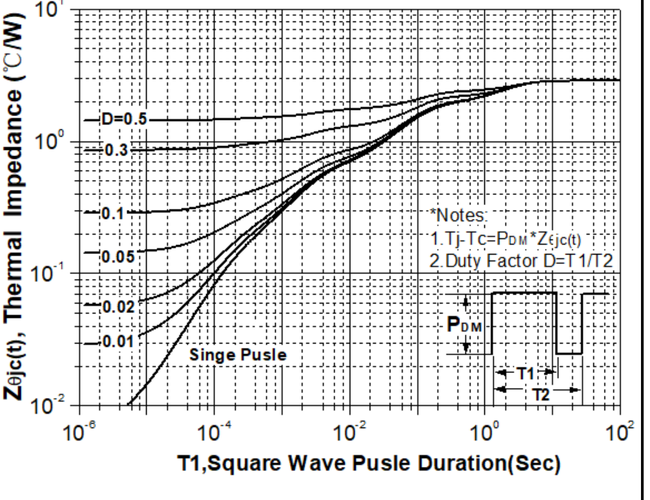
<table>
<tr><th>Power dissipation（TO220F）</th><th>Max.transient thermal impedance（TO220F）</th></tr>
<tr><td>
</td><td>
</td></tr>
<tr><td>$P_{tot}=f(T_C)$</td><td>$Z_{thJC}=f(t_P)$;parameter:$D=t_P/T$</td></tr>
</table>

Table 9 Output Characteristics

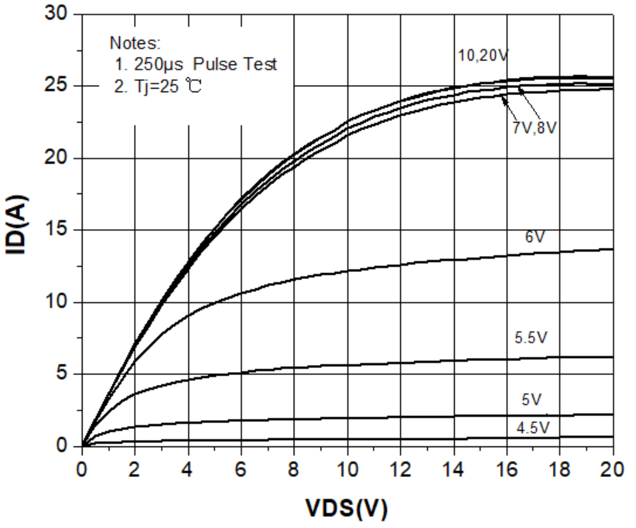
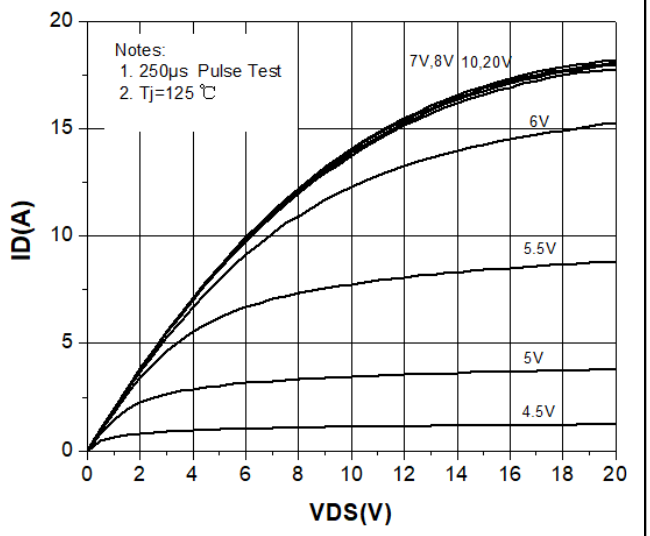
Typical output characteristics T_J= 25°C	Typical output characteristics T_J= 125°C
	
I_D=f(V_{DS}); T_j = 25°C ;parameter:V_{GS}	I_D=f(V_{DS}); T_j = 125°C ;parameter:V_{GS}

Table 10 Drain Source Resistance

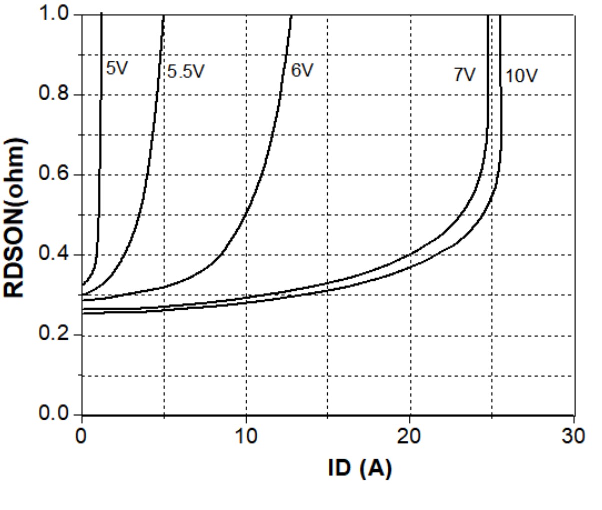
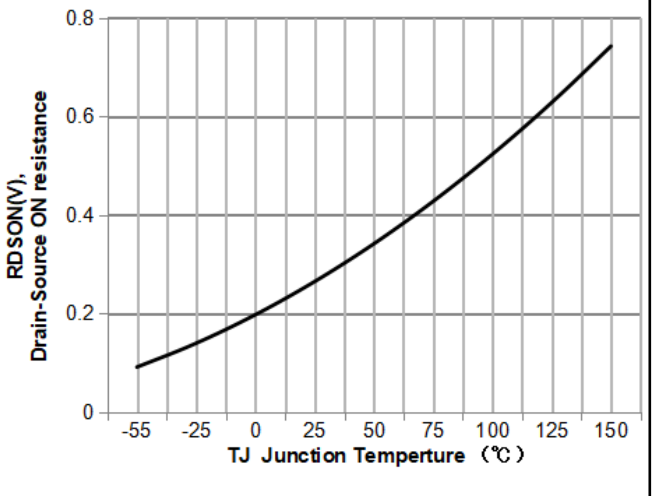
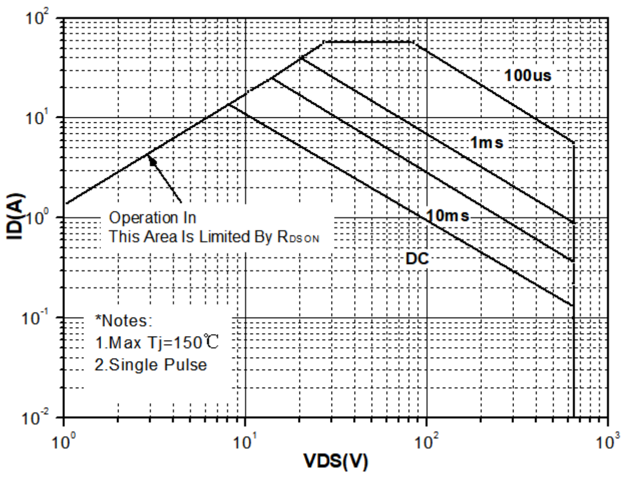
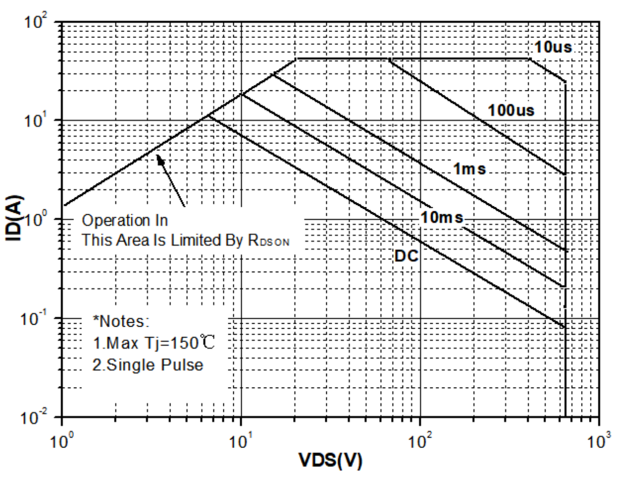
Typical drain-source on-state resistance	Drain-source on-state resistance
	
$R_{DS(On)}$=f(I_D); T_j = 25°C parameter:V_{GS}	$R_{DS(On)}$=f(T_j); I_D = 7.1A :V_{GS}=10V

Table 11 Safe Operating Area

<table>
<tr><td>Safe operating area T_C= 25ºC（TO220, TO263 & TO247）</td><td>Safe operating area T_C= 80ºC（TO220, TO263 & TO247）</td></tr>
<tr><td>
</td><td>
</td></tr>
<tr><td>I_D=f(V_{DS}); T_C = 25ºC ;D=0;parameter:t_P</td><td>I_D=f(V_{DS}); T_C = 80ºC ;D=0;parameter:t_P</td></tr>
</table>

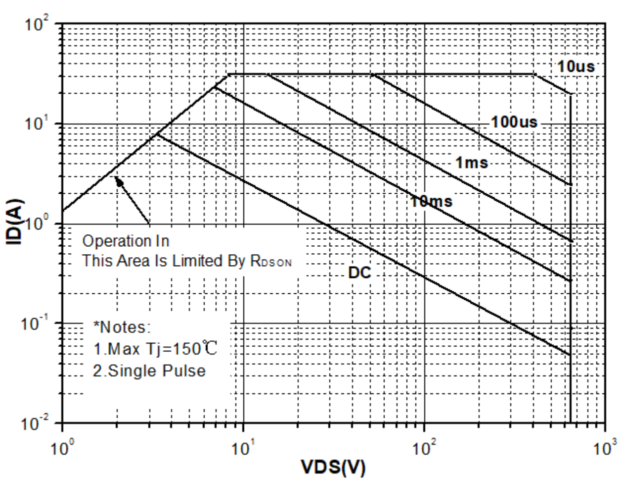
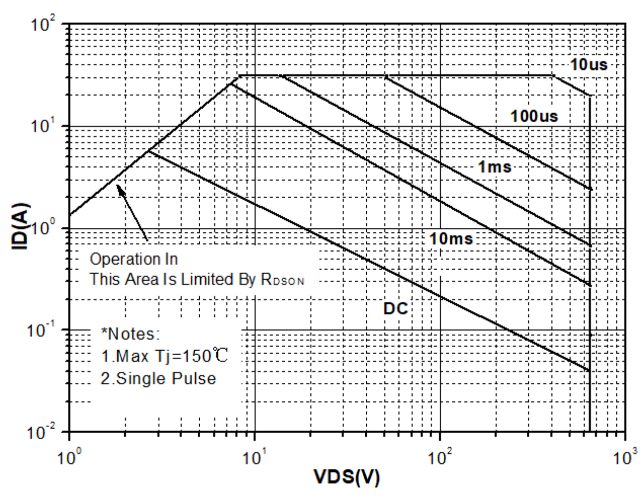
<table>
<tr><td>Safe operating area T_C= 25ºC（TO220F）</td><td>Safe operating area T_C= 80ºC（TO220F)</td></tr>
<tr><td>
</td><td>
</td></tr>
<tr><td>I_D=f(V_{DS}); T_C = 25ºC ;D=0;parameter:t_P</td><td>I_D=f(V_{DS}); T_C = 80ºC ;D=0;parameter:t_P</td></tr>
</table>

Table 12 Capacitances and Gate Charge

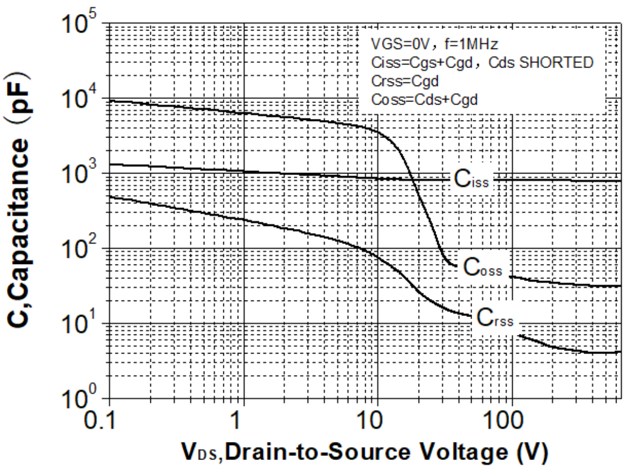
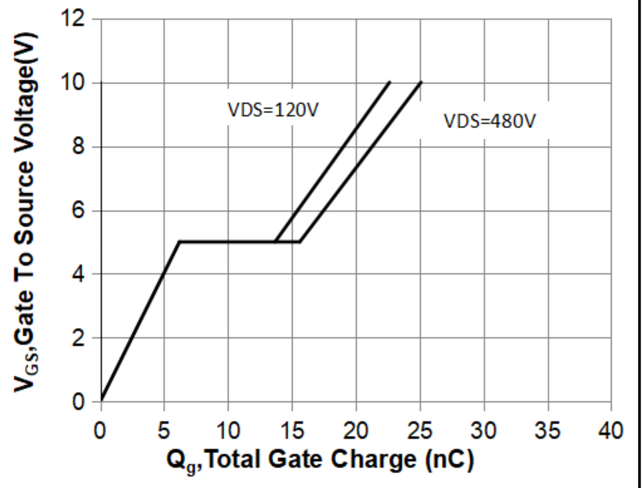
Typical Capacitances	Typical Gate charge
	
V_{gs}=0v, Freq.= 1MHz	I_D=f(Q_{gate}); I_D = 7.1A pulsed; parameter:V_{DD}

Table 13 Diode Characteristics and Avalanche Energy

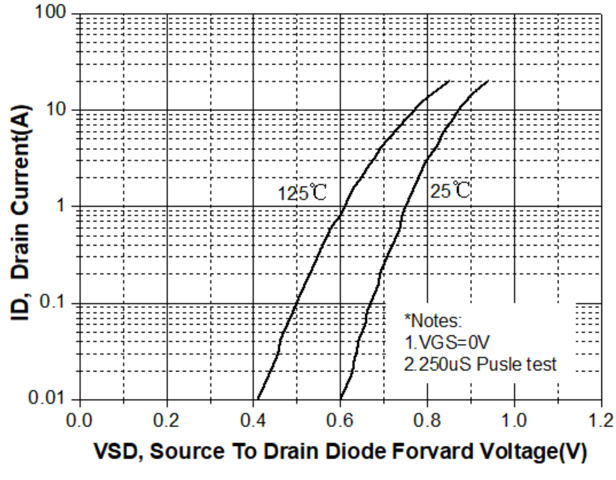
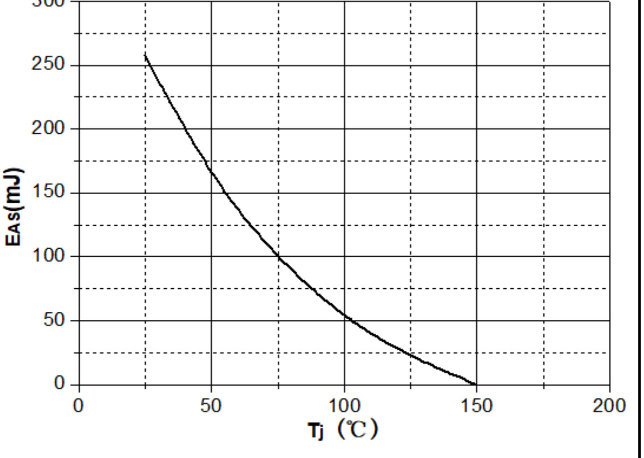
Forward characteristics of reverse diode	Avalanche energy
	
I_F=f(V_{SD}); parameter:T_j	E_{AS}=f(T_j); I_D = 2.4A ; V_{DD} = 50V

Table 14 Breakdown Voltage and Transfer Characteristics

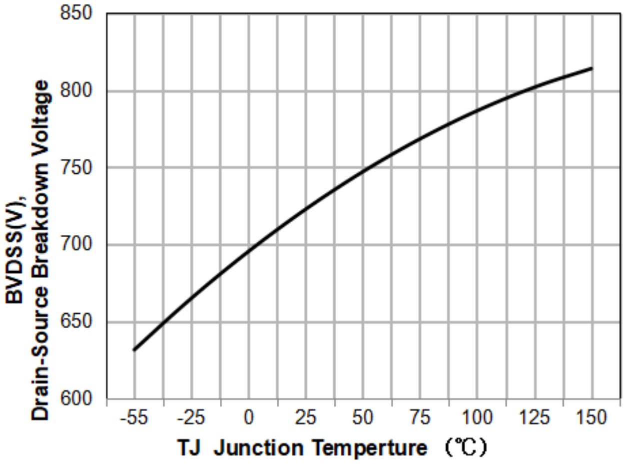
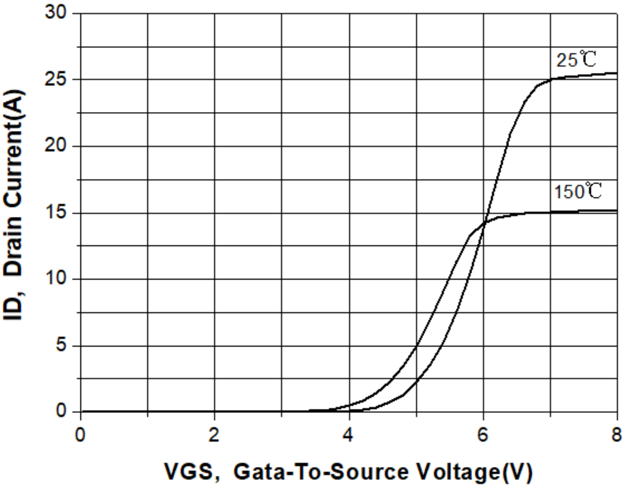
Drain-source breakdown voltage	Transfer Characteristics
	
$V_{BR(DSS)}=f(T_j)$; $I_D = 0.25mA$	$I_D=f(V_{GS})$; $\lvert V_{DS}\rvert >2\lvert I_D\rvert R_{DS(On)max}$;parameter:$T_j$

Table 15 Diode Recovery Characteristic

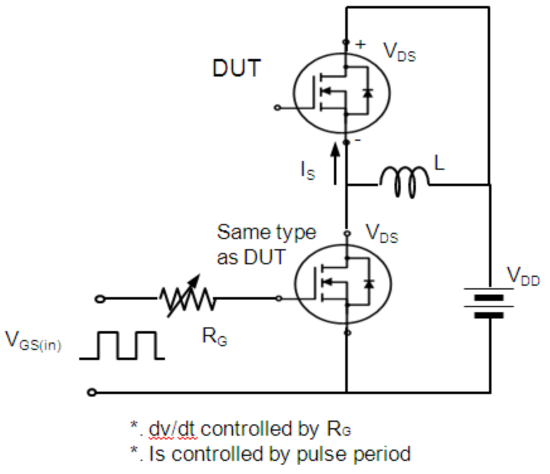
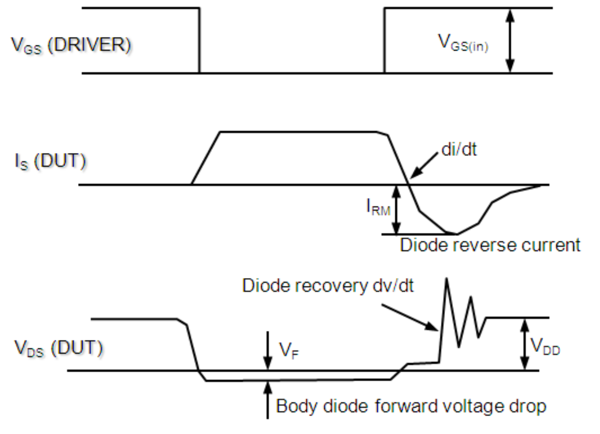
Test Circuit For Diode Recovery	Test Waveform For Diode Recovery
	

Table 16 Switching Time Characteristic

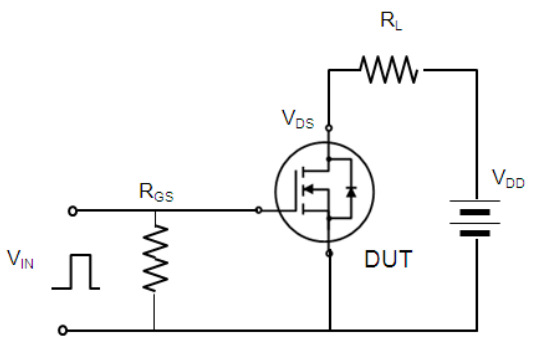
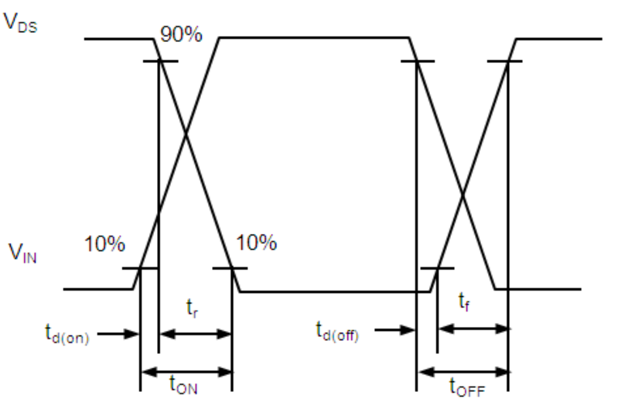
Test Circuit for Switching Time	Test Waveform for Switching Time
	

Table 17 Gate Charge Characteristic

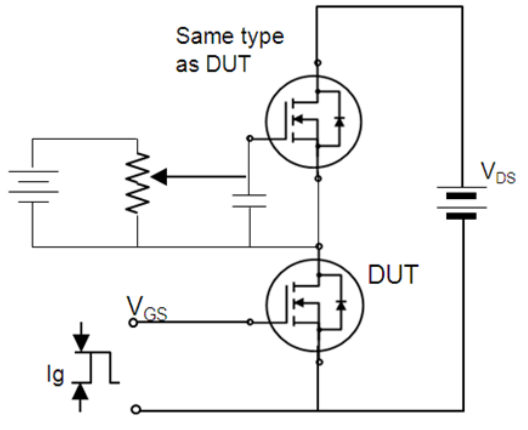
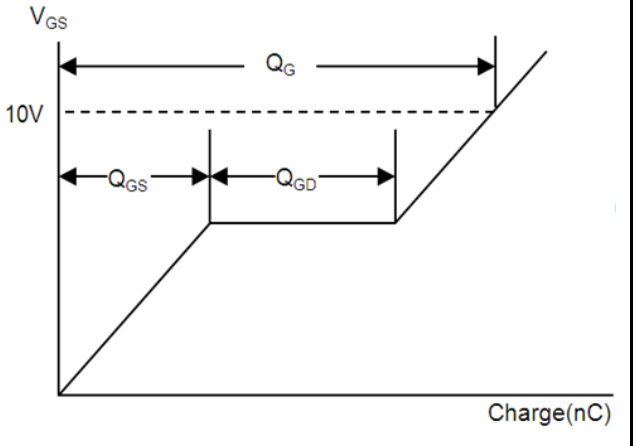
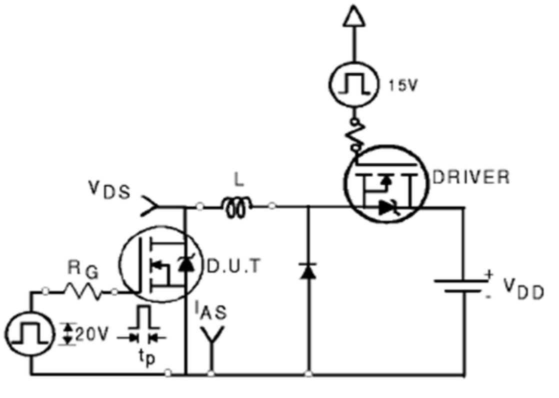
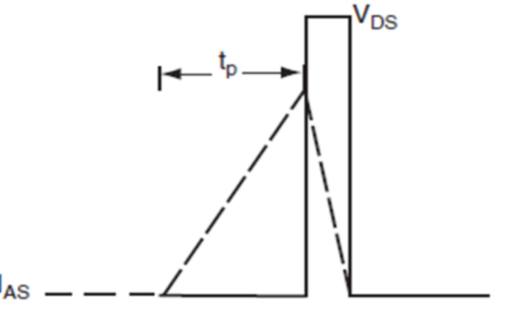
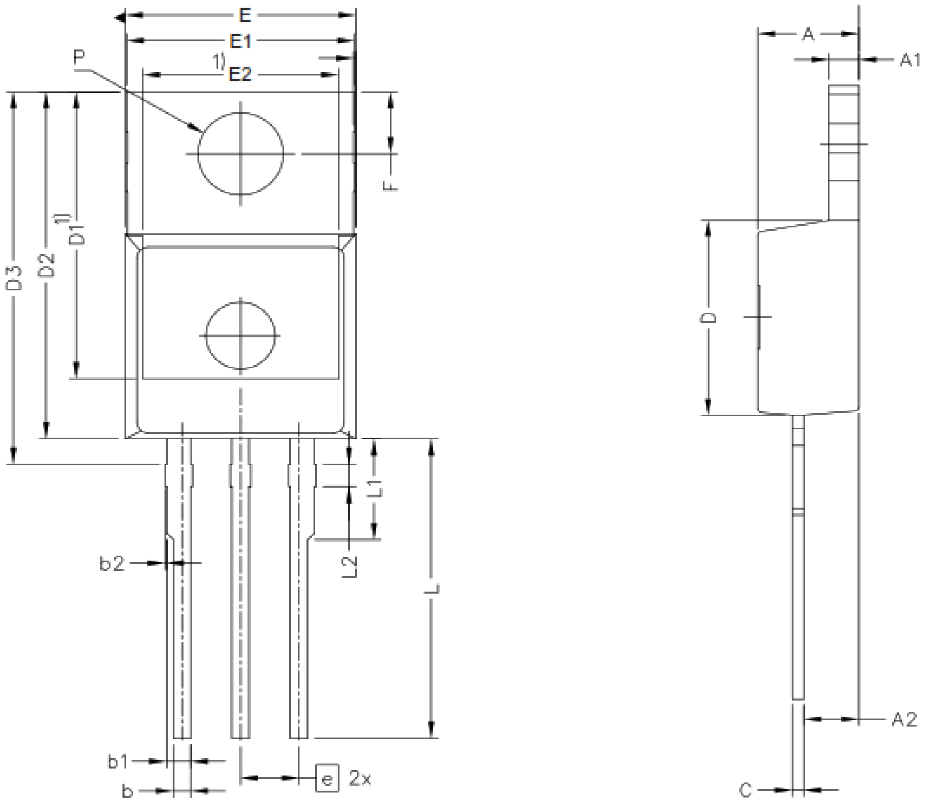
Test Circuit For Gate Charge	Test Waveform For Gate Charge
	

Table 18 Unclamped Inductive Characteristic

Test Circuit For Unclamped Inductive	Test Waveform For Unclamped Inductive
	$E_{AS} = \frac{1}{2} L I_{AS}^2$ 

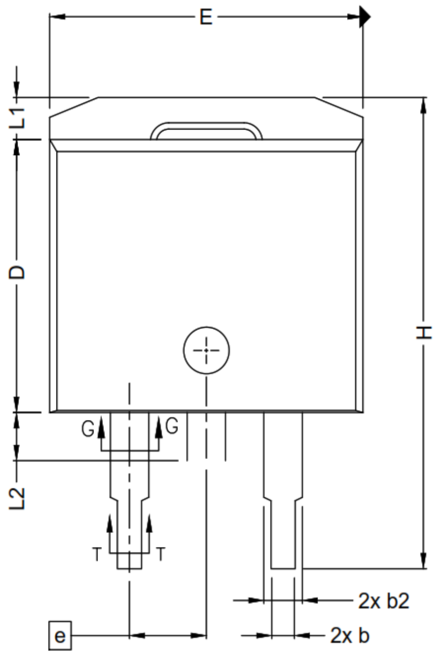
4a) TO-220

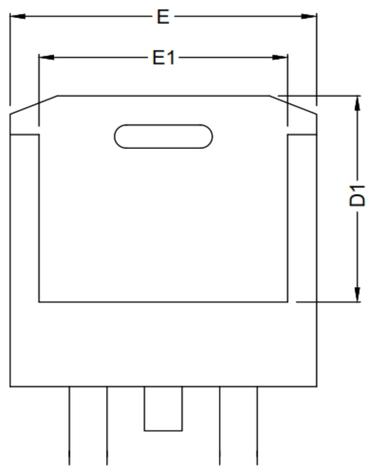


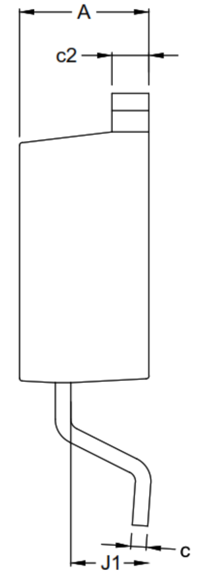
TO-220 3L

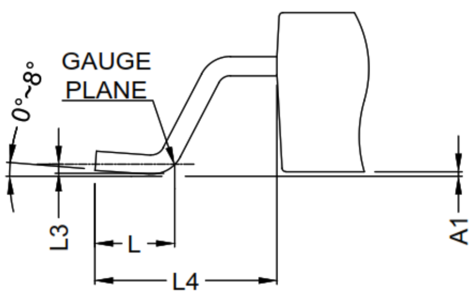
SYMBOL	MIN	MAX
A	4.20	4.60
A1	1.20	1.40
A2	2.20	2.60
b	0.65	0.85
b1	0.95	1.15
b2		0.15
C	0.40	0.60
D	9.05	9.45
D1	12.95	
D2	15.35	15.95
D3	16.50	17.10
E	9.80	10.20
E1	9.70	10.10
E2	8.50	
e	2.46	2.54
F	2.60	3.00
L	13.00	14.00
L1	4.35	4.75
L2	0.90	1.10
P	3.55	3.85

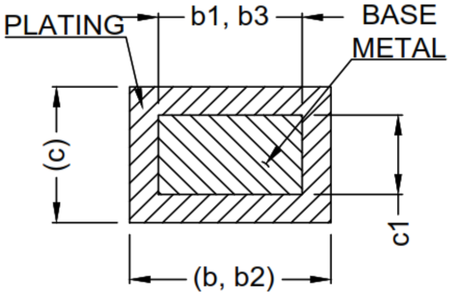
4b) TO-263







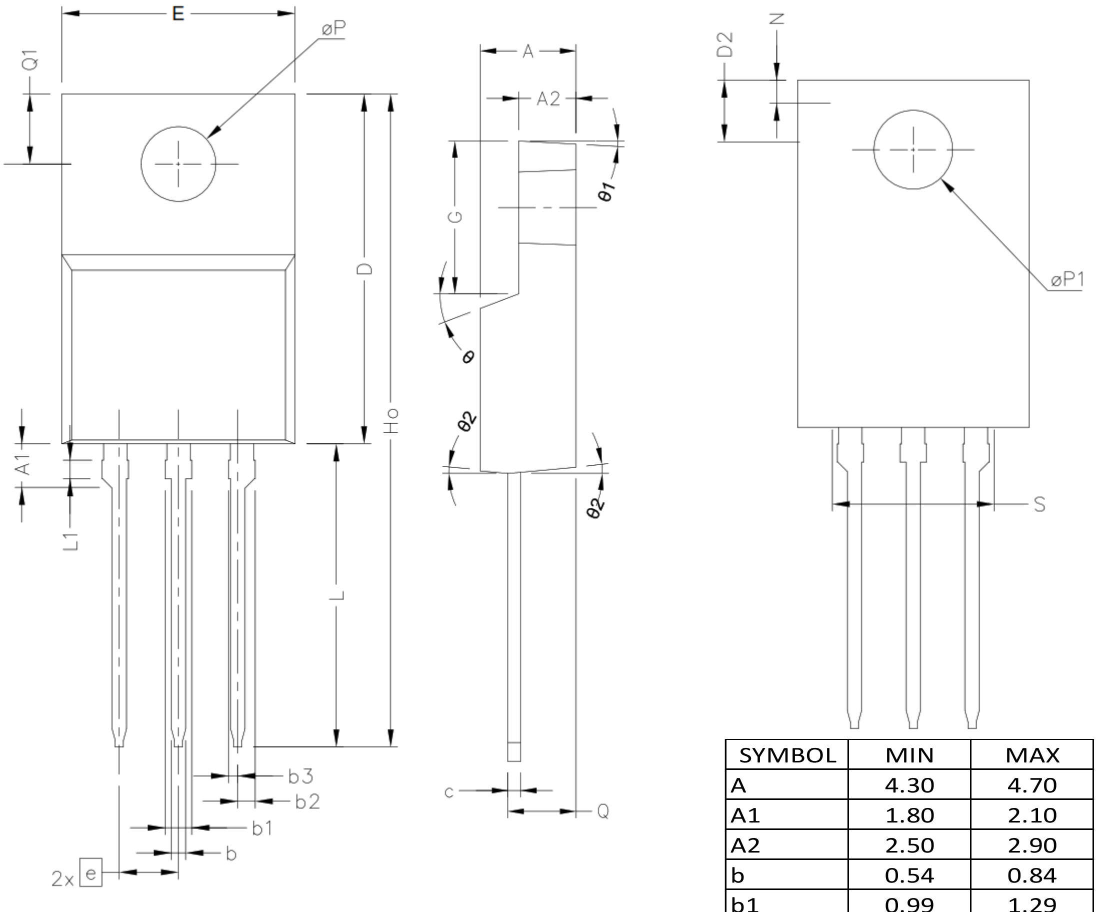




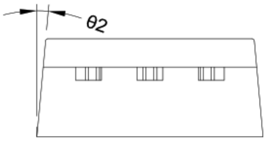
TO-263 (D2PAK)

SYMBOL	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.7	0.9
b1	0.51	0.89
b2	1.2	1.46
b3	1.17	1.37
c	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.6	9
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
e	2.46	2.54
H	15	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25 TYP	
L4	4.78	5.28
J1	2.56	2.96

4C) TO-220 FullPak



SYMBOL	MIN	MAX
A	4.30	4.70
A1	1.80	2.10
A2	2.50	2.90
b	0.54	0.84
b1	0.99	1.29
b2	0.56	0.93
b3	0.24	0.55
c	0.49	0.79
D	14.70	15.30
D2	2.66	
e	2.29	2.79
E	9.70	10.30
G	6.70	7.10
Ho	28.00	
L	12.50	13.50
L1	0.70	0.90
N	2.86	
øP	3.05	3.40
øP1	3.40	
Q	3.10	3.30
Q1	2.70	3.30
S	7.00	
Θ1	3 deg.	
Θ2	5 deg.	



Revision History

Revision	Release Date	Comments
1.0	1-Nov 2016	Preliminary Datasheet Draft
1.5	15-June 2017	Update tables
2.0	6-Dec 2017	Update tables, characterization
2.1	11-Dec 2017	Updated Parameters
3.0	2-Jan 2019	Recharacterization and tables

Resources

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